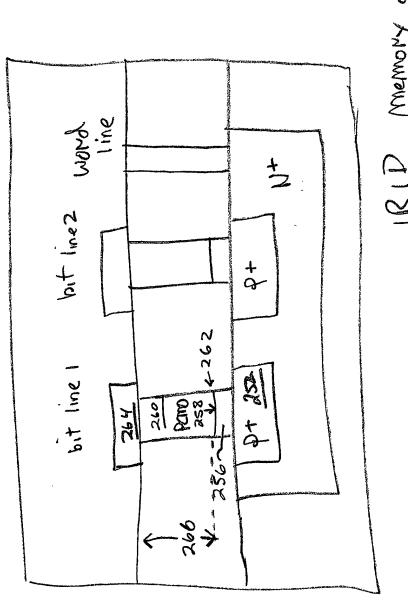


IRIT MEMORY amay

F19.20

35



IRID (MEMONY ONTAX

acetic acid injected onto water surface spin at 1500 to 3000 Mpm for 30 seconds 0.05m Pemo solution injected onto water surface Spin at 1500 to 3000 rpm for 30 seconds 0.25m Pemo solution injected onto water surface (manual or auto dispense) spin speed : 500 upm Spin at 1500 to 3000 rpm for 30 seconds cycles bake at 180°c for immute bake at 2300 for 1 minute RTA anneal at 500°c for Sminutes

post anneal at 800-600°C for 1-6 hours in dry clean air

F15.3

1

acetic acid injected onto wafer surface spin at 1500 to 3000 rpm for 30 seconds 0.05M PCMO solution injected onto wafer surface spin at 1500 to 3000 rpm for 30 seconds 0.25M PCMO solution injected onto wafer surface (manual or auto dispense) spin speed: 500 rpm spin at 1500 to 3000 rpm for 30 seconds cycles baking at 180 °C for 1 minute baking at 230 °C for 1 minute RTA-anneal at 500 °C for 5 minute

Fig. 4

post-anneal at 500 - 600 °C for 1 - 6 hours in dry clean air

SARF torring substrate growing feature, morroral to substrate with acetic acid 1st Pemo solution 2nd Remo Solution 5510 annealing 5/3 5512a baking et 130-180° Er 1 minute baking at 200-250°c for 1 minute 5126 RTA at 400-600° for 2-15 minutes Post-annealing Forming Pemo film 1516 Fig. 5